

HFA1212/883

PRELIMINARY

June 1994

Dual, High Speed, Low Power, Video Closed Loop Buffer

Features

- This Circuit is Processed in Accordance to MIL-STD-883 and is Fully Conformant Under the Provisions of Paragraph 1.2.1.
- User Programmable For Closed-Loop Gains of +1, -1 or +2 Without Use of External Resistors
- Standard Operational Amplifier Pinout
- Low Supply Current..... 5.9mA/Op Amp (Typ)
- Excellent Gain Accuracy......0.99V/V (Typ)
- Wide -3dB Bandwidth 340MHz (Typ)
- High Input Impedance 1MΩ (Typ)
- Excellent Gain Flatness (to 50MHz) ±0.02dB (Typ)
- Fast Overdrive Recovery.....<10ns (Typ)

Applications

- Flash A/D Driver
- Video Switching and Routing
- · Pulse and Video Amplifiers
- Wideband Amplifiers
- · RF/IF Signal Processing
- Medical Imaging Systems

Description

The HFA1212/883 is a dual closed loop Buffer featuring user programmable gain and high speed performance. Manufactured on Intersil's proprietary complementary bipolar UHF-1 process, this device offers wide -3dB bandwidth of 340MHz, very fast slew rate, excellent gain flatness and high output current.

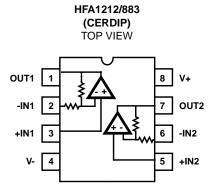
A unique feature of the pinout allows the user to select a voltage gain of +1, -1, or +2, without the use of any external components. Gain selection is accomplished via connections to the inputs, as described in the "Application Information" section. The result is a more flexible product, fewer part types in inventory, and more efficient use of board space.

Compatibility with existing op amp pinouts provides flexibility to upgrade low gain amplifiers, while decreasing component count. Unlike most buffers, the standard pinout provides an upgrade path should a higher closed loop gain be needed at a future date.

Ordering Information

PART NUMBER	TEMPERATURE RANGE	PACKAGE
HFA1212MJ/883	-55°C to +125°C	8 Lead CerDIP

Pinout



Specifications HFA1212/883

Absolute Maximum Ratings

Thermal Information

Voltage Between V+ and V	Thermal Resista CerDIP Packa
Output Current (Note 1) Short Circuit Protected	Maximum Packa
Output Current (50% Duty Cycle, Note 1)	CerDIP Packa
Junction Temperature	Package Power
ESD Rating> 2000V	CerDIP Packa
Storage Temperature Range -65° C \leq $T_{A} \leq +150^{\circ}$ C	
Lead Temperature (Soldering 10s)+300°C	

Thermal Resistance	θ_{JA}	θ_{JC}
CerDIP Package	115°C/W	30°C/W
Maximum Package Power Dissipation at +	-75°C	
CerDIP Package		0.87W
Package Power Dissipation Derating Factor	or above +75	5°C
CerDIP Package		8.7mW/ ^o C

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Operating Conditions

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_{SOURCE} = 0\Omega$, $R_L = 100\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS		
PARAMETERS	ARAMETERS SYMBOL CONDITIONS		SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
		V _{CM} = 0V	1	+25°C	-10	10	mV
Voltage			2, 3	+125°C, -55°C	-20	20	mV
Channel-to-Channel	ΔV _{OS}	V _{CM} = 0V	1	+25°C	-15	15	mV
Output Offset Voltage Mismatch			2, 3	+125°C, -55°C	-30	30	mV
Common Mode	CMRR	$\Delta V_{CM} = \pm 1.8V$	1	+25°C	42	-	dB
Rejection Ratio		V+ = 3.2V, V- = -6.8V V+ = 6.8V, V- = -3.2V	2	+125°C	39	-	dB
		$\Delta V_{CM} = \pm 1.2V$ V+ = 3.8V, V- = -6.2V V+ = 6.2V, V- = -3.8V	3	-55°C	39	-	dB
Power Supply Rejection Ratio PSRRP PSRRN	PSRRP	$\Delta V_{SUPPLY} = \pm 1.8V$ V+ = 6.8V, V- = -5V V+ = 3.2V, V- = -5V	1	+25°C	45	-	dB
			2	+125°C	42	-	dB
	ΔV _{SUPPLY} = ±1.2V V+ = 6.2V, V- = -5V V+ = 3.8V, V- = -5V	3	-55°C	42	-	dB	
	PSRRN	301111	1	+25°C	45	-	dB
	V+ = 5V, V- = -6.8V V+ = 5V, V- = -3.2V	2	+125°C	42	-	dB	
		ΔV _{SUPPLY} = ±1.2V V+ = 5V, V- = -6.2V V+ = 5V, V- = -3.8V	3	-55°C	42	-	dB
Non-Inverting Input (+IN) Current	I _{BSP}	V _{CM} = 0V	1	+25°C	-15	15	μΑ
			2, 3	+125°C, -55°C	-25	25	μΑ
Channel-to-Channel +IN Current	ΔI_{BSP}	V _{CM} = 0V	1	+25°C	-15	15	μΑ
Mismatch			2, 3	+125°C, -55°C	-25	25	μΑ

Specifications HFA1212/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_{SOURCE} = 0\Omega$, $R_L = 100\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

				GROUP A		LIMITS		
PARAMETERS	SYMBOL	CONI	DITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
+IN Current Common	CMS _{IBP}	$\Delta V_{CM} = \pm 1.8$	$\Delta V_{CM} = \pm 1.8V$		+25°C	-	1.25	μA/V
Mode Sensitivity		V+ = 3.2V, V- = -6.8V V+ = 6.8V, V- = -3.2V		2	+125°C	-	2.85	μΑ/V
		$\Delta V_{CM} = \pm 1.2V$ V+ = 3.8V, V- = -6.2V V+ = 6.2V, V- = -3.8V		3	-55°C	-	2.85	μA/V
+IN Resistance	+R _{IN}	Note 2		1	+25°C	800	-	kΩ
				2, 3	+125°C, -55°C	350	-	kΩ
Gain	A _{VP1}	A _V = +1	. 417	1	+25°C	0.98	1.02	V/V
		$V_{IN} = -1V$ to	+1V	2, 3	+125°C, -55°C	0.975	1.025	V/V
	A _{VM1}	$A_{V} = -1$ $V_{IN} = -1 V \text{ to}$. 417	1	+25°C	-0.98	-1.02	V/V
		$V_{IN} = -1 V to$	+1V	2, 3	+125°C, -55°C	-0.975	-1.025	V/V
	A _{VP2}	A_{VP2} $A_{V} = +2$ $V_{IN} = -1V \text{ to } +1V$		1	+25°C	1.96	2.04	V/V
				2, 3	+125°C, -55°C	1.95	2.05	V/V
Channel-to-Channel	ΔA_{VP1}	$A_{V} = +1$ $V_{IN} = -1V \text{ to } +1V$		1	+25°C	-0.02	0.02	V/V
Gain Mismatch ΔA _{VM1}				2, 3	+125°C, -55°C	-0.025	0.025	V/V
	ΔA_{VM1}	V _{IN} = -1V to +1V		1	+25°C	-0.025	0.025	V/V
				2, 3	+125°C, -55°C	-0.025	0.025	V/V
	ΔA_{VP2}			1	+25°C	-0.04	0.04	V/V
				2, 3	+125°C, -55°C	-0.05	0.05	V/V
Output Voltage V _{OP100}	V _{OP100}	$A_V = -1$	V _{IN} = -3.2V	1	+25°C	3	-	V
Swing		$A_{V} = -1$ $R_{L} = 100\Omega$	V _{IN} = -3V	2, 3	+125°C, -55°C	2.8	-	V
	V _{ON100}		$V_{IN} = +3.2V$	1	+25°C	-	-3	V
			V _{IN} = +3V	2, 3	+125°C, -55°C	-	-2.8	V
Output Voltage	V _{OP50}	$A_{V} = -1$ $R_{L} = 50\Omega$	V _{IN} = -2.7V	1	+25°C	2.5	-	V
Swing			V _{IN} = -2.25V	2	+125°C	2.0	-	V
			V _{IN} = -2.25V	3	-55°C	1.4	-	V
	V _{ON50}	A _V = -1	V _{IN} = +2.7V	1	+25°C	-	-2.5	V
		$R_L = 50\Omega$	V _{IN} = +2.25 V	2	+125°C	-	-2.0	V
			V _{IN} = +2.25	3	-55°C	-	-1.4	V

Specifications HFA1212/883

TABLE 1. DC ELECTRICAL PERFORMANCE CHARACTERISTICS (Continued)

Device Tested at: $V_{SUPPLY} = \pm 5V$, $A_V = +1$, $R_{SOURCE} = 0\Omega$, $R_L = 100\Omega$, $V_{OUT} = 0V$, Unless Otherwise Specified.

			GROUP A		LIMITS		
PARAMETERS	SYMBOL	CONDITIONS	SUBGROUPS	TEMPERATURE	MIN	MAX	UNITS
Output Current	+l _{OUT}	Note 3	1	+25°C	50	-	mA
			2	+125°C	40	-	mA
			3	-55°C	28	-	mA
	-l _{OUT}	Note 3	1	+25°C	-	-50	mA
			2	+125°C	-	-40	mA
			3	-55°C	-	-28	mA
Quiescent Power	I _{CC}	$R_L = 100\Omega$	1	+25°C	5.6	6.1	mA/Op Amp
Supply Current			2, 3	+125°C, -55°C	5.2	6.5	mA/Op Amp
	I _{EE}	$R_L = 100\Omega$	1	+25°C	-6.1	-5.6	mA/Op Amp
			2, 3	+125°C, -55°C	-6.5	-5.2	mA/Op Amp

NOTES:

- 1. Output is short circuit protected to ground. Brief short circuits to ground will not degrade reliability, however continuous (100% duty cycle) output current must not exceed 30mA for maximum reliability.
- 2. Guaranteed from +IN Common Mode Rejection Test, by: $+R_{IN} = 1/CMS_{IBP}$.
- 3. Guaranteed from $\rm V_{OUT}$ Test with $\rm R_L$ = $50\Omega,$ by: $\rm I_{OUT}$ = $\rm V_{OUT}/50\Omega.$

TABLE 2. AC ELECTRICAL PERFORMANCE CHARACTERISTICS

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TABLE 3. ELECTRICAL PERFORMANCE CHARACTERISTICS

Table 3 Intentionally Left Blank.

TABLE 4. ELECTRICAL TEST REQUIREMENTS

MIL-STD-883 TEST REQUIREMENTS	SUBGROUPS (SEE TABLE 1)
Interim Electrical Parameters (Pre Burn-In)	1
Final Electrical Test Parameters	1(Note 1), 2, 3
Group A Test Requirements	1, 2, 3
Groups C and D Endpoints	1

NOTE:

1. PDA applies to Subgroup 1 only.

Die Characteristics

DIE DIMENSIONS:

 $69 \text{ x } 92 \text{ x } 19 \text{ mils } \pm 1 \text{ mils}$ 1750 x 2330 x 483 μ m \pm 25.4 μ m

METALLIZATION:

Type: Metal 1: AlCu(2%)/TiW Type: Metal 2: AlCu(2%)

Thickness: Metal 1: $8k\mathring{A} \pm 0.4k\mathring{A}$ Thickness: Metal 2: $16k\mathring{A} \pm 0.8k\mathring{A}$

GLASSIVATION: Type: Nitride

Thickness: 4kÅ ± 0.5kÅ

WORST CASE CURRENT DENSITY:

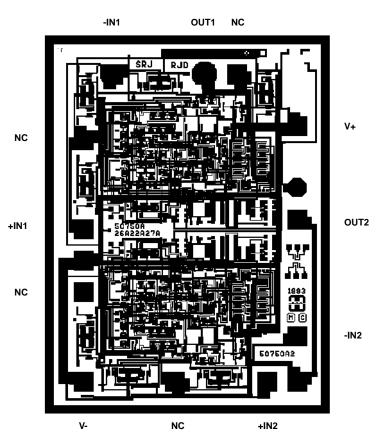
TBD

TRANSISTOR COUNT: 150

SUBSTRATE POTENTIAL (Powered Up): Floating (Recommend Connection to V-)

Metallization Mask Layout

HFA1212/883



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